

MMBTH10Q

#### 25V NPN SURFACE MOUNT VHF/UHF TRANSISTOR IN SOT23

### **Description**

This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

### **Features**

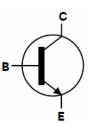
- BV<sub>CEO</sub> > 25V
- I<sub>C</sub> = 50mA Continuous Collector Current
- Designed for VHF/UHF Amplifier Applications and High Output VHF Oscillators
- High Current Gain Bandwidth Product
- Ideal for Mixer and RF Amplifier Applications with Collector Currents in the 100µA to 30mA Range
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Mechanical Data**

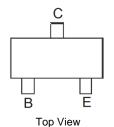
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads, Solderable per MIL-STD-202. Method 208 <sup>3</sup>
- Weight: 0.008 grams (Approximate)







Device Symbol



Pin-Out

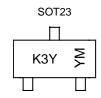
Ordering Information (Note 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMBTH10Q-7-F	Automotive	K3Y	7	8	3000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

### **Marking Information**



K3Y = Product Type Marking Code YM = Date Code Marking Y = Year ex: F = 2018 M = Month ex: 9 = September

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	F	G	H		J	K	L	М	N	0	Р	Q
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	2	4	5	6	7	8	a	0	N	D

MMBTH10Q
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## Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	30	V
Collector-Emitter Voltage	V <sub>CEO</sub>	25	V
Emitter-Base Voltage	$V_{EBO}$	3	V
Collector Current	lc	50	mA

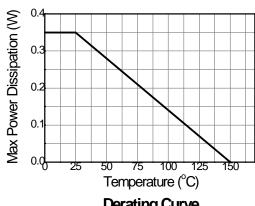
## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	2	310	mW	
Power Dissipation	(Note 7)	P <sub>D</sub>	350	11100	
Thormal Desigtance, Junction to Ambient	(Note 6)	_	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>OJA</sub>	357		
Thermal Resistance, Junction to Leads (Note 8)		$R_{\Theta JL}$	350	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C		

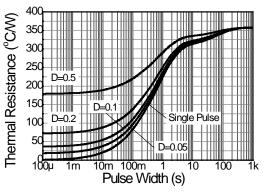
Notes:

- 6. For a device mounted on minimum recommended pad layout FR-4 PCB with high coverage of single sided 1oz copper; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as Note 6, except mounted on 15mm x 15mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

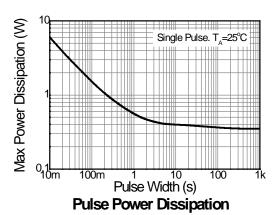
## **Thermal Characteristics and Derating Information**







**Transient Thermal Impedance** 





## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	30	_	_	V	$I_C = 100\mu A$	
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	25	_	_	V	$I_C = 1mA$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	3	_	_	V	I <sub>C</sub> = 100μA	
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	_	100	nA	V <sub>CB</sub> = 25V	
Emitter-Base Cut-Off Current	I <sub>EBO</sub>	_	_	100	nA	V <sub>EB</sub> = 2V	
ON CHARACTERISTICS (Note 9)							
DC Current Gain	h <sub>FE</sub>	60		_	_	$V_{CE} = 10V$ , $I_C = 4mA$	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	0.5	V	$I_C = 4mA, I_B = 400\mu A$	
Base-Emitter Voltage	V <sub>BE(SAT)</sub>	_	_	0.95	V	$I_C = 4mA, I_B = 400\mu A$	
Base-Emitter Turn-on Voltage	V <sub>BE(ON)</sub>	_	_	0.95	V	$V_{CE} = 10V$ , $I_C = 4mA$	
SMALL SIGNAL CHARACTERISTICS							
Current Gain Bandwidth Product	f <sub>T</sub>	650	_	_	MHz	$V_{CE} = 10V, I_{C} = 4mA,$ f = 100MHz	
Collector-Base Capacitance	Ссво	_	_	0.7	pF	V <sub>CB</sub> = 10V, f = 1MHz	
Collector-Base Feedback Capacitance	C <sub>RBO</sub>			0.65	pF	$V_{CB} = 10V$ , $f = 1MHz$	
Collector-Base Time Constant	Rb'Cc	_	_	9	ps	V <sub>CB</sub> = 10V, f = 31.8MHz, I <sub>C</sub> = 4mA	

Note 9: Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

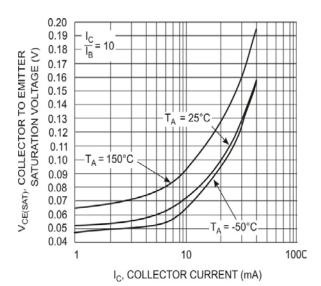


Fig. 1 Collector Emitter Saturation Voltage vs. Collector Current

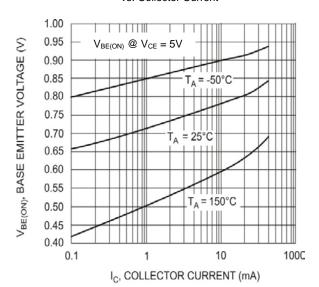


Fig. 3 Base Emitter Voltage vs. Collector Current

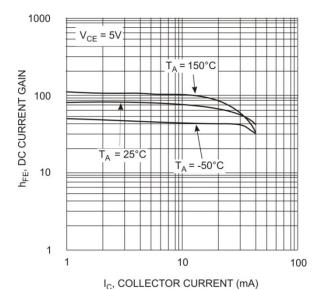


Fig. 2 DC Current Gain vs. Collector Current

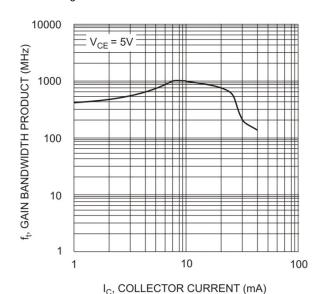
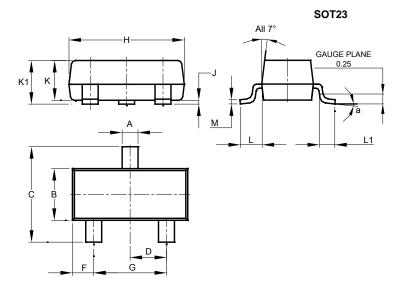


Fig. 4 Gain Bandwidth Product vs. Collector Current



## **Package Outline Dimensions**

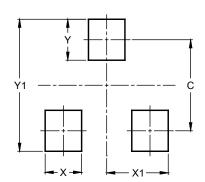
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### SOT23

Dimensions	Value (in mm)
C	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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